



## UT4414

Power MOSFET

### N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

#### DESCRIPTION

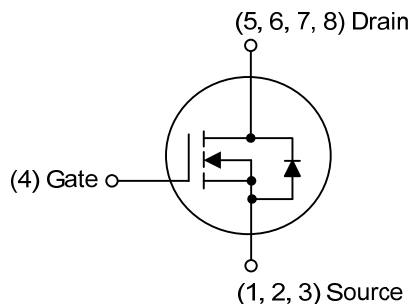
The UTC **UT4414** is an N-channel enhancement mode FET with excellent trench technology to provide customers perfect  $R_{DS(ON)}$  and low gate charge. The source leads are separated to allow a Kelvin connection to the source, which may be used to bypass the source inductance.

This device can be applied in a load switch or in PWM applications.

#### FEATURES

- \*  $V_{DSS} = 30V$
- \*  $I_D = 8.5A$  @  $V_{GS} = 10V$
- \*  $R_{DS(ON)} < 26m\Omega$  @  $V_{GS} = 10V, I_D = 8.5A$
- \*  $R_{DS(ON)} < 40m\Omega$  @  $V_{GS} = 4.5V, I_D = 5A$

#### SYMBOL



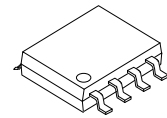
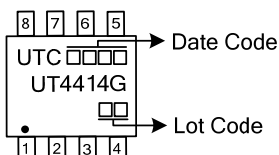
#### ORDERING INFORMATION

Ordering Number	Package	Pin Assignment								Packing
		1	2	3	4	5	6	7	8	
UT4414G-S08-R	SOP-8	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

UT4414G-S08-R	(1) Packing Type (2) Package Type (3) Green Package	(1) R: Tape Reel (2) S08: SOP-8 (3) G: Halogen Free and Lead Free
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#### MARKING



SOP-8

■ ABSOLUTE MAXIMUM RATING ( $T_A = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain to Source Voltage		$V_{DSS}$	30	V
Gate to Source Voltage		$V_{GSS}$	$\pm 20$	V
Continuous Drain Current (Note 1)	$T_A = 25^\circ\text{C}$	$I_D$	8.5	A
	$T_A = 70^\circ\text{C}$	$I_D$	7.1	A
Pulsed Drain Current (Note 1)		$I_{DM}$	50	A
Total Power Dissipation	$T_A = 25^\circ\text{C}$	$P_D$	3	W
	$T_A = 70^\circ\text{C}$		2.1	W
Junction Temperature		$T_J$	+150	$^\circ\text{C}$
Storage Temperature		$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER		SYMBOL	MIN	TYP	MAX	UNIT
Junction to Ambient (Note 1)	$t \leq 10\text{s}$	$\theta_{JA}$		31	40	$^\circ\text{C/W}$
	Steady-State			59	75	$^\circ\text{C/W}$

■ ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	30			V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V		0.004	1	μA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V ,V <sub>GS</sub> =±20V			100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA	1	1.9	3	V
On State Drain Current	I <sub>D(ON)</sub>	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =5V	20			A
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =8.5A		20	26	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A		31	40	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =5A	10	17		S
DYNAMIC PARAMETERS						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f =1MHz		680	820	pF
Output Capacitance	C <sub>OSS</sub>			102		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			77		pF
Gate Resistance	R <sub>G</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f =1MHz		3	3.6	Ω
SWITCHING PARAMETERS						
Total Gate Charge (10V)	Q <sub>G</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =10V, I <sub>D</sub> =8.5A		13.84	17	nC
Total Gate Charge (4.5V)	Q <sub>G</sub>			6.74	8.1	nC
Gate-Source Charge	Q <sub>GS</sub>			1.84		nC
Gate-Drain Charge	Q <sub>GD</sub>			3.32		nC
Turn-ON Delay Time	t <sub>D(ON)</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =10V, R <sub>G</sub> =3Ω, R <sub>L</sub> =1.8Ω		4.5	6.5	ns
Turn-ON Rise Time	t <sub>R</sub>			4.2	6.3	ns
Turn-OFF Delay Time	t <sub>D(OFF)</sub>			20.1	30	ns
Turn-OFF Fall Time	t <sub>F</sub>			4.9	7.5	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I <sub>S</sub>				4.3	A
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.76	1	V
Body Diode Reverse Recovery Time	t <sub>RR</sub>	I <sub>F</sub> =8.5A, dI/dt=100A/μs		17.2	21	ns
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	I <sub>F</sub> =8.5A, dI/dt=100A/μs		8.6	10	nC

Notes: 1. The value of  $\theta_{JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any given application depends on the user's specific board design.

The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.

2. Repetitive Rating : Pulse width limited by  $T_J$ .

3. The  $\theta_{JA}$  is the sum of the thermal impedance from junction to lead  $\theta_{JL}$  and lead to ambient.

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